

BYQ60W-600PT2

Ultrafast power diode

Rev.03 - 22 May 2023

Product data sheet

1. General description

Ultrafast power diode in a TO247-2L plastic package.

2. Features and benefits

- · Fast switching and soft reverse recovery characteristics
- Low forward voltage drop
- Low leakage current
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT
- High operating temperature capability (T_{i (max)} = 175°C)

3. Applications

- UPS
- EV Charger
- Welding Machine
- Air Conditioner

4. Quick reference data

| Table 1. Q | uick reference data | | | | | | |
|---|---------------------------------|---|--------|-----|------|-----|------|
| Symbol | Parameter | Conditions | Values | | | | Unit |
| Absolute | maximum rating | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | | 6 | 00 | | V |
| $I_{F(AV)}$ | average forward current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 129 °C; Fig. 1; Fig. 2; Fig. 3 | 60 | | | A | |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 129 °C; square-wave pulse | 120 | | A | | |
| I _{FSM} non-repetitive peak forward current | | t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; <u>Fig. 4</u> | 600 / | | | A | |
| | | t_{p} = 8.3 ms; $T_{\text{j(init)}}$ = 25 °C; sine-wave pulse | 660 | | А | | |
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| Static ch | aracteristics | | | | | | |
| V _F | forward voltage | I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u> | | - | 1.55 | 2 | V |
| | | I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u> | | - | 1.2 | 1.6 | V |
| Dynamic | characteristics | | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | | - | - | 55 | ns |

5. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--------------------|-------------------------------|
| 1 | К | cathode | | |
| 2 | А | anode | | K <u>– K</u> – A 001aaa020 |
| mb | mb | mounting base; connected to cathode | TO247-2L | |

6. Ordering information

| Table 3. Ordering information | | | | | | | | |
|-------------------------------|-----------------|-----------------------|----------------|---------------------------|-----------------|-----------------------|--|--|
| Type number | Package Name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date | | |
| BYQ60W-600PT2 | TO247-2L | BYQ60W-600PT2Q | Tube | 30 | TO247L-2L (L) | 12-Nov-2020 | | |
| | | | | | TO247P-2L (P) | 31-Mar-2023 | | |

600PT2

PJLxxxx xx

7. Marking

Table 4. Marking codes Type number Marking codes Assembly factory: L BYQ60W-600PT2 BYQ60W

Assembly factory: P

BYQ60W

600PT2

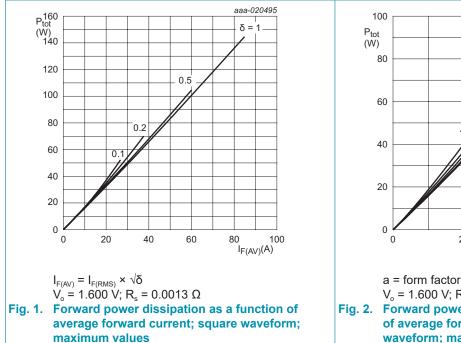
PJPxxxx xx

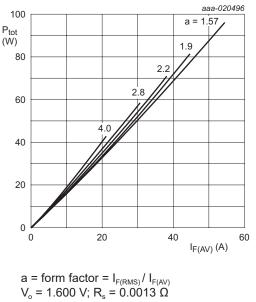
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

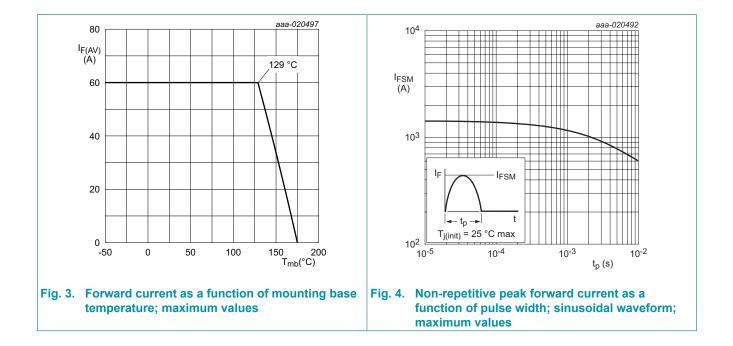
| Symbol | Parameter | Conditions | Values | Unit |
|----------------------|--|--|------------|------------------|
| V _{RRM} | repetitive peak reverse voltage | | 600 | V |
| V_{RWM} | crest working reverse voltage | | 600 | V |
| V _R | reverse voltage | DC | 600 | V |
| $\mathbf{I}_{F(AV)}$ | average forward current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 129 °C; Fig. 1; Fig. 2; Fig. 3 | 60 | A |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 129 °C; square-wave pulse | 120 | A |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4 | 600 | A |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 660 | A |
| l ² t | limiting Joule-integral | SIN; t _p = 10 ms | 1800 | A ² s |
| T _{stg} | storage temperature | | -55 to 175 | °C |
| Tj | junction temperature | | 175 | °C |





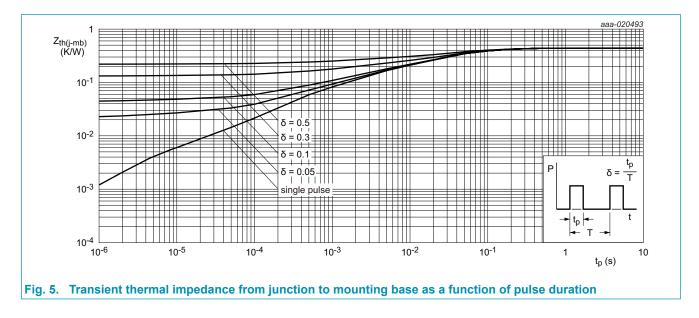
V_o = 1.000 V; R_s = 0.0013 Ω
 Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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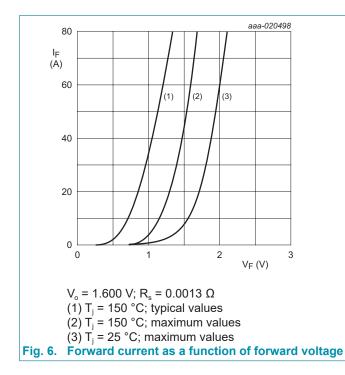
9. Thermal characteristics

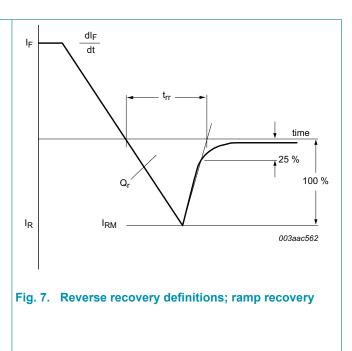
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|---------------|-----|-----|------|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance from junction to mounting base | <u>Fig. 5</u> | - | - | 0.44 | K/W |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient free air | in free air | - | 45 | - | K/W |



10. Characteristics

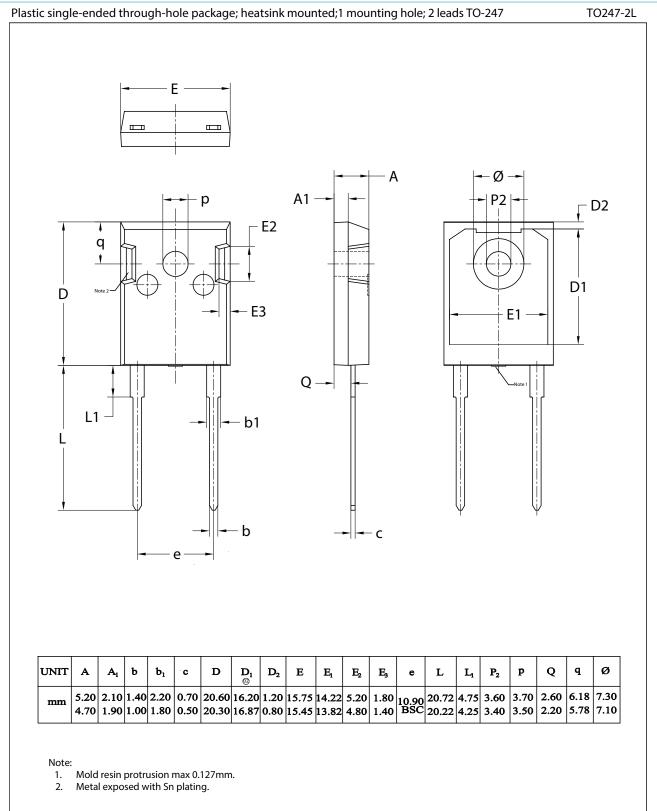
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|----------------------------------|--|-----|------|-----|------|
| Static ch | aracteristics | | I | | | |
| V _F | forward current | I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u> | - | 1.55 | 2 | V |
| | | I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u> | - | 1.2 | 1.6 | V |
| I _R | reverse current | V _R = 600 V; T _j = 25 °C | - | - | 10 | μA |
| | | V _R = 600 V; T _j = 125 °C | - | - | 500 | μA |
| Dynamic | characteristics | · · · · · | | | | |
| Qr | reverse charge | $ I_F = 60 \text{ A}; \text{V}_R = 400 \text{ V}; \text{d}_F/\text{d}t = 200 \text{ A}/\mu\text{s}; \\ \text{T}_j = 25 ^\circ\text{C}; \overline{\text{Fig. } 7} $ | - | 143 | - | nC |
| | | $I_F = 60 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$ | - | 876 | - | nC |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$ | - | - | 55 | ns |
| | | $I_F = 60 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 53 | - | ns |
| | | $I_F = 60 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$ | - | 120 | - | ns |
| I _{RM} | peak reverse recovery current | $I_F = 60 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 5.4 | - | A |
| | | I _F = 60 A; V _R = 400 V; dI _F /dt = 200 A/μs; T _i = 125 °C; <u>Fig. 7</u> | - | 14.5 | - | А |



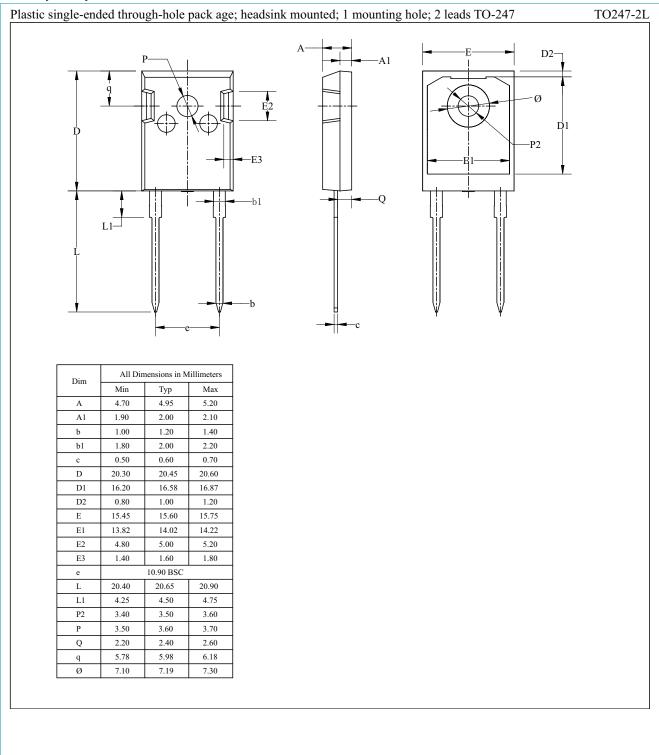


11. Package outline

Assembly factory: L



Assembly factory: P



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Ultrafast power diode

12. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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